



**Datenblatt  
data sheet**

**Höchstzulässige Werte / Maximum rated values**

**Elektrische Eigenschaften / Electrical properties**

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = -25^{\circ}\text{C}$	$V_{CES}$	3300 3300	V V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C,nom.}$ $I_C$	800 1300	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^{\circ}\text{C}$	$I_{CRM}$	1600	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$ , Transistor	$P_{tot}$	9,6	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/- 20V	V
Dauergleichstrom DC forward current		$I_F$	800	A
Periodischer Spitzenstrom repetitive peak forw. Current	$t_p = 1\text{ ms}$	$I_{FRM}$	1600	A
Grenzlastintegral der Diode I2t - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	222.200	A <sup>2</sup> s
Spitzenverlustleistung der Diode maximum power dissipation diode	$T_{vj} = 125^{\circ}\text{C}$	$P_{RQM}$	800	kW
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	$V_{ISOL}$	6.000	V
Teilentladungs-Aussetzspannung partial discharge extinction voltage	RMS, $f = 50\text{ Hz}, Q_{PD} \leq 10\text{ pC}$ (acc. to IEC 1287)	$V_{ISOL}$	2.600	V

**Charakteristische Werte / Characteristic values**

**Transistor / Transistor**

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 800\text{ A}, V_{GE} = 15\text{V}, T_{vj} = 25^{\circ}\text{C}$	$V_{CE\text{ sat}}$	-	3,40	4,25	V
	$I_C = 800\text{ A}, V_{GE} = 15\text{V}, T_{vj} = 125^{\circ}\text{C}$		-	4,30	5,00	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	$V_{GE(th)}$	4,2	5,1	6,0	V
Eingangskapazität input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{ies}$	-	100	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{res}$	-	5,4	-	nF
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}, V_{CE} = 1800\text{V}$	$Q_G$	-	15	-	$\mu\text{C}$
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 3300\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$	$I_{CES}$	-	0,1	8	mA
	$V_{CE} = 3300\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^{\circ}\text{C}$		-	40	100	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$	$I_{GES}$	-	-	400	nA

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date of publication : 08.06.99

approved by: Chr. Lübke; 20.07.99

revision: 2



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Charakteristische Werte / Characteristic values

			min.	typ.	max.	
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}$	$t_{d,on}$	-	370	-	ns
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 25^\circ \text{ C}$					
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}$	$t_r$	-	250	-	ns
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 25^\circ \text{ C}$					
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}$	$t_{d,off}$	-	1550	-	ns
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 25^\circ \text{ C}$					
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}$	$t_f$	-	200	-	ns
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 25^\circ \text{ C}$					
	$V_{GE} = \pm 15 \text{ V}, R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}, V_{GE} = 15 \text{ V}$ $R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}, L_S = 40 \text{ nH}$	$E_{on}$	-	1920	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 800 \text{ A}, V_{CC} = 1800 \text{ V}, V_{GE} = 15 \text{ V}$ $R_G = 1,8 \Omega, C_{GE} = 150 \text{ nF}, T_{vj} = 125^\circ \text{ C}, L_S = 40 \text{ nH}$	$E_{off}$	-	1020	-	mWs
Kurzschlußverhalten SC Data	$t_p \leq 10 \mu\text{sec}, V_{GE} \leq 15 \text{ V}$	$I_{SC}$	-	4000	-	A
	$T_{vj} \leq 125^\circ \text{ C}, V_{CC} = 2500 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$					
Modulinduktivität stray inductance module	IGBT (Zweig / arm 1+2 parallel )	$L_{sCE}$	-	12	-	nH
	Diode (Zweig / arm 3)					
Modul-Leitungswiderstand, Anschlüsse - Chip lead resistance, terminals - chip	$T = 25^\circ \text{ C}, \text{IGBT (Zweig / arm 1+2 parallel )}$	$R_{CC+EE}$	-	0,19	-	mΩ
	$T = 25^\circ \text{ C}, \text{Diode (Zweig / arm 3)}$					

Charakteristische Werte / Characteristic values

			min.	typ.	max.	
Durchlaßspannung forward voltage	$I_F = 800 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 25^\circ \text{ C}$	$V_F$	-	2,80	3,50	V
	$I_F = 800 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 125^\circ \text{ C}$					
Sperrstrom reverse current	$V_{CE} = 3300 \text{ V}, T_{vj} = 25^\circ \text{ C}, \text{Zweig / arm 3}$	$I_R$	-	0,01	1,6	mA
	$V_{CE} = 3300 \text{ V}, T_{vj} = 125^\circ \text{ C}, \text{Zweig / arm 3}$					
Rückstromspitze peak reverse recovery current	$I_F = 800 \text{ A}, - di_F/dt = 2500 \text{ A}/\mu\text{sec}$	$I_{RM}$	-	650	-	A
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 25^\circ \text{ C}$					
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 125^\circ \text{ C}$					
Sperrverzögerungsladung recovered charge	$I_F = 800 \text{ A}, - di_F/dt = 2500 \text{ A}/\mu\text{sec}$	$Q_r$	-	500	-	μAs
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 25^\circ \text{ C}$					
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 125^\circ \text{ C}$					
Abschaltenergie pro Puls reverse recovery energy	$I_F = 800 \text{ A}, - di_F/dt = 2500 \text{ A}/\mu\text{sec}$	$E_{rec}$	-	490	-	mWs
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 25^\circ \text{ C}$					
	$V_R = 1800 \text{ V}, V_{GE} = -10 \text{ V}, T_{vj} = 125^\circ \text{ C}$					



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**Thermische Eigenschaften / Thermal properties**

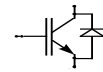
		min.    typ.    max.				
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	$R_{thJC}$	-	-	0,013	K/W
	Diode/Diode, DC, Zweig / arm 1+2		-	-	0,026	K/W
	Diode/Diode, DC, Zweig / arm 3		-	-	0,026	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{paste} = 1 \text{ W/m}^2\text{K} / \lambda_{grease} = 1 \text{ W/m}^2\text{K}$	$R_{thCK}$	-	0,004	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj}$	-	-	150	°C
Betriebstemperatur operation temperature		$T_{op}$	-40	-	125	°C
Lagertemperatur storage temperature		$T_{stg}$	-40	-	125	°C

**Mechanische Eigenschaften / Mechanical properties**

Gehäuse, siehe Anlage case, see appendix				
Material Modulgrundplatte material of module baseplate			AlSiC	
Innere Isolation internal insulation			AlN	
Kriechstrecke creepage distance			32,2	mm
Luftstrecke clearance			19,1	mm
CTI comperative tracking index			> 400	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M1	5	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	terminals M4	M2	2	Nm
	terminals M8		8 .. 10	Nm
Gewicht weight		G	1500	g

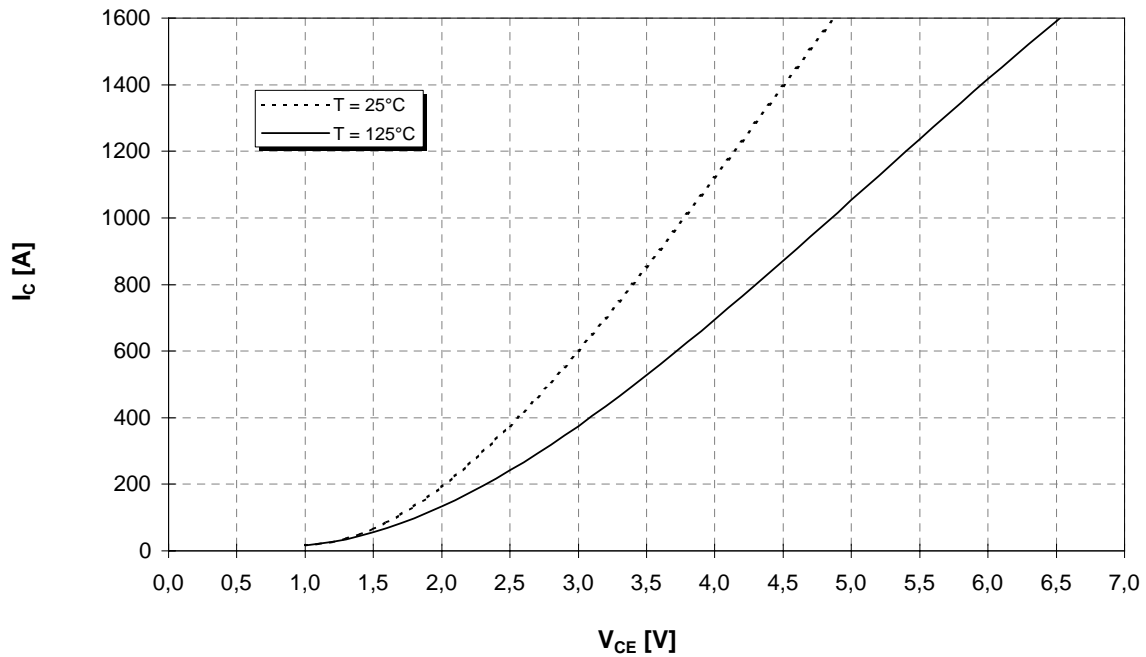
Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert.  
Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



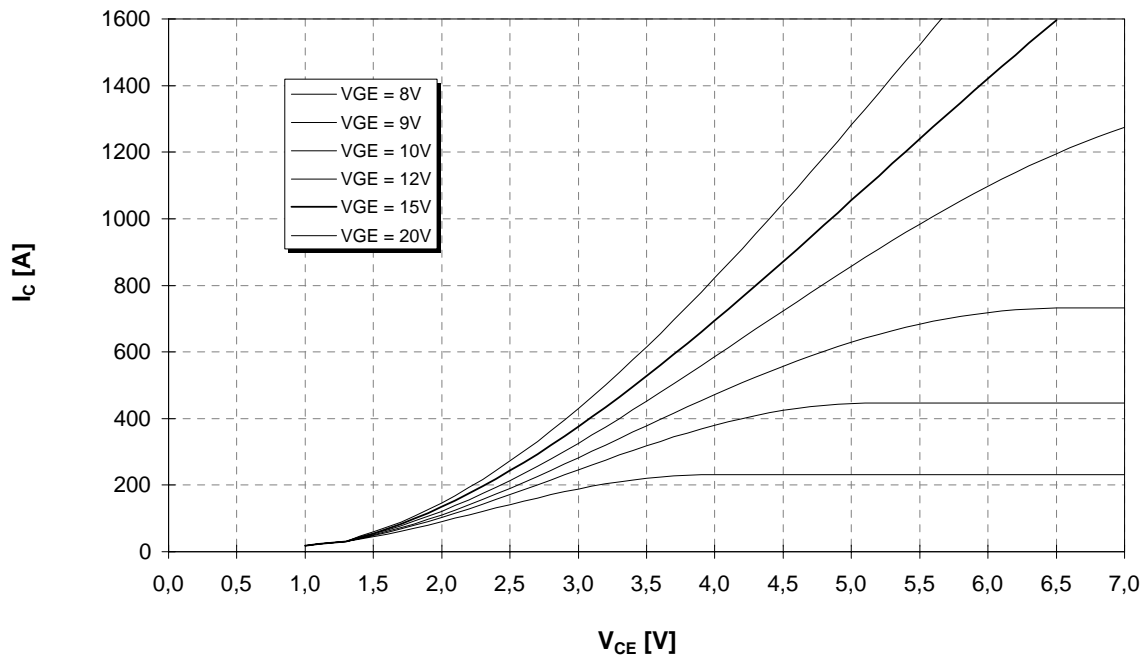
**Ausgangskennlinie (typisch)**  
**Output characteristic (typical)**

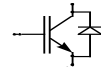
$I_C = f(V_{CE})$   
 $V_{GE} = 15V$



**Ausgangskennlinienfeld (typisch)**  
**Output characteristic (typical)**

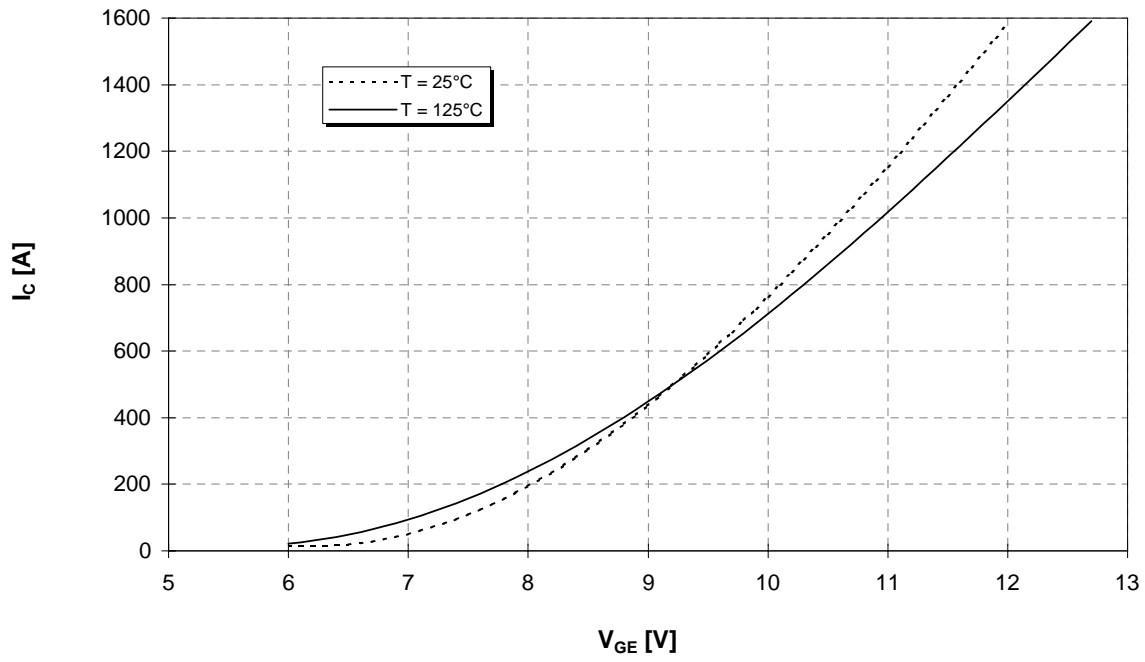
$I_C = f(V_{CE})$   
 $T_{vj} = 125^\circ C$





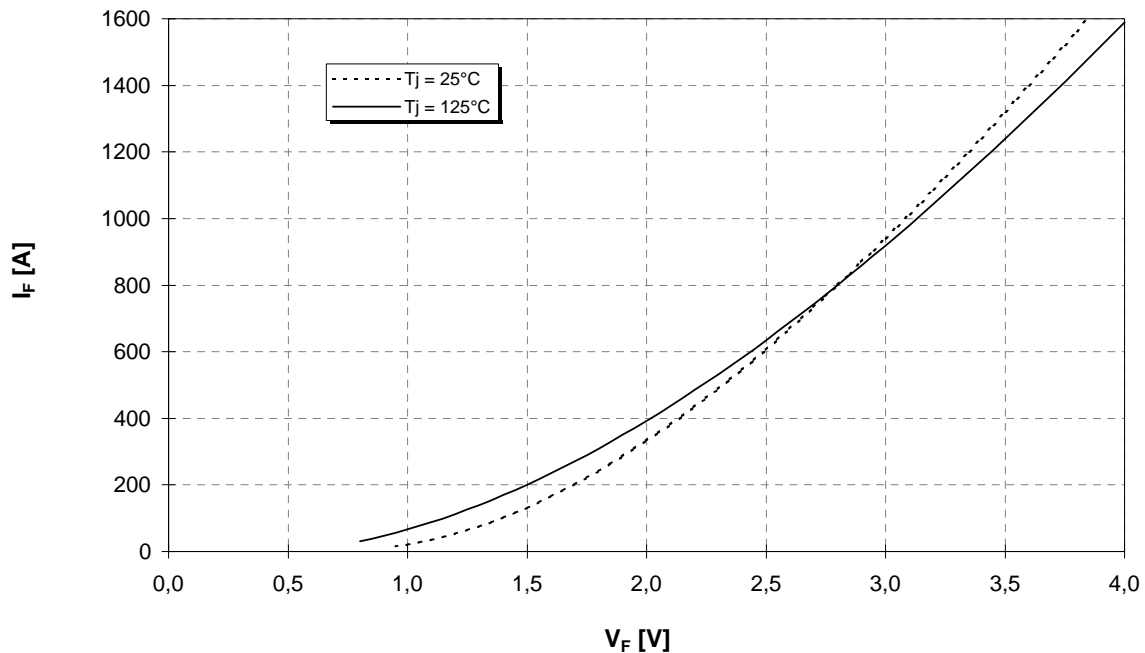
Übertragungscharakteristik (typisch)  
Transfer characteristic (typical)

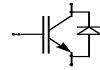
$I_C = f(V_{GE})$   
 $V_{CE} = 20V$



Durchlaßkennlinie der Inversdiode (typisch)  
Forward characteristic of inverse diode (typical)

$I_F = f(V_F)$

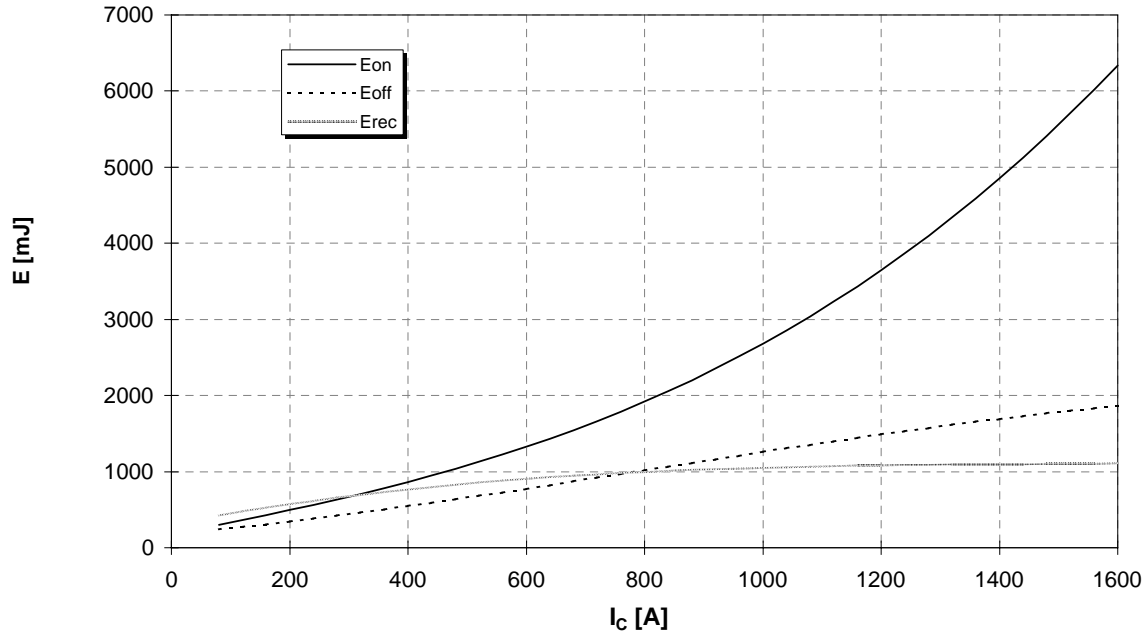




Schaltverluste (typisch)  
Switching losses (typical)

$$E_{on} = f(I_C), E_{off} = f(I_C), E_{rec} = f(I_C)$$

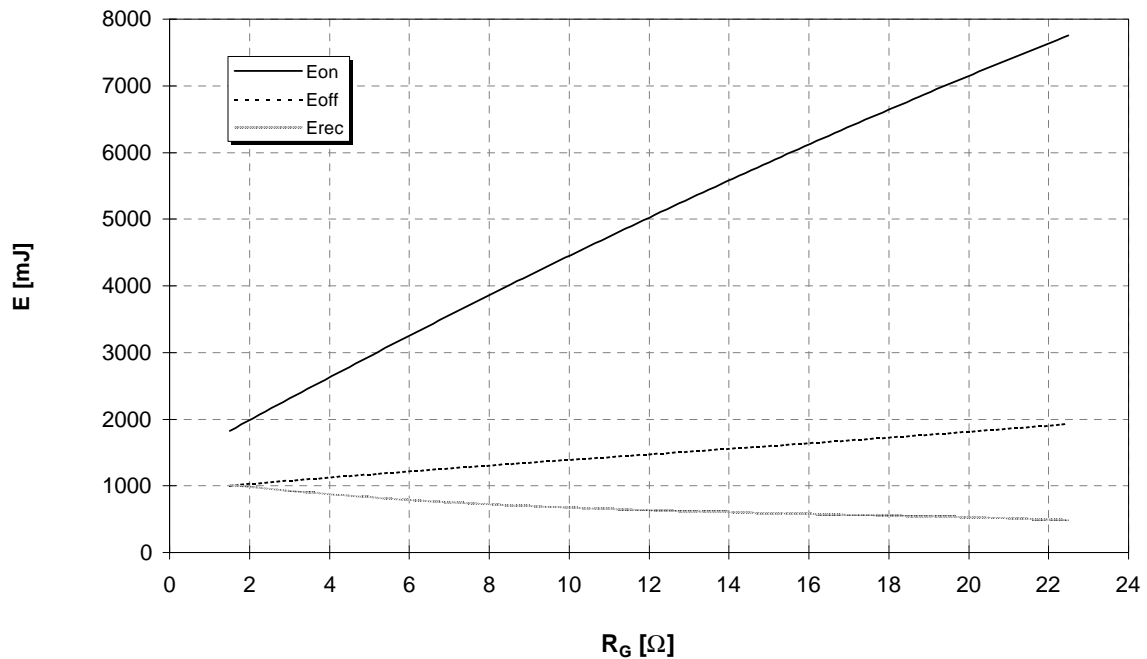
$R_{G,on} = 1,8 \Omega, R_{G,off} = 1,8 \Omega, C_{GE} = 150 \text{ nF}, V_{CE} = 1800 \text{ V}, T_j = 125^\circ \text{C}$

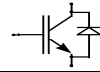


Schaltverluste (typisch)  
Switching losses (typical)

$$E_{on} = f(R_G), E_{off} = f(R_G), E_{rec} = f(R_G)$$

$I_C = 800 \text{ A}, C_{GE} = 150 \text{ nF}, V_{CE} = 1800 \text{ V}, T_j = 125^\circ \text{C}$



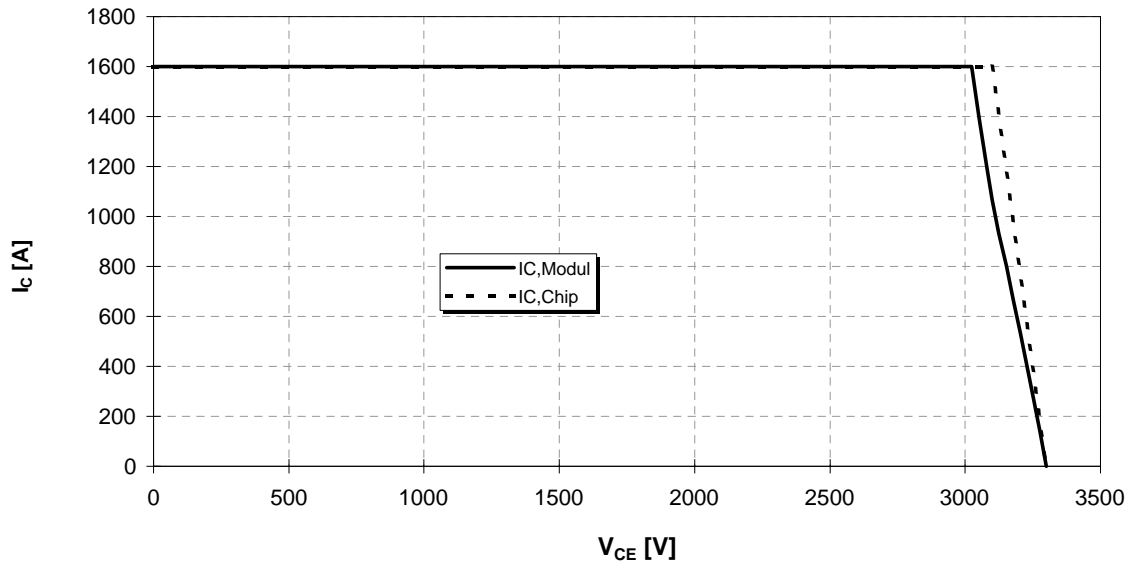


**Sicherer Arbeitsbereich IGBT (RBSOA)**

**Reverse bias safe operation area IGBT (RBSOA)**

$R_{G,off} = 1,8 \Omega$ ,  $C_{GE} = 150 \text{ nF}$

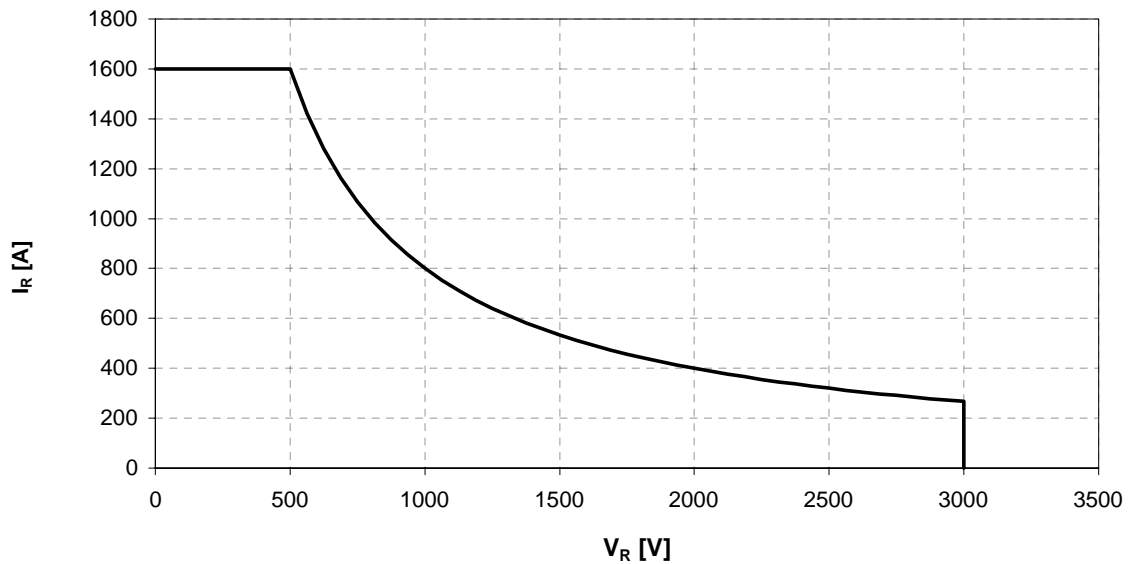
$T_{vj} = 125^\circ\text{C}$

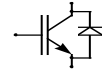


**Sicherer Arbeitsbereich Diode (SOA)**

**safe operation area Diode (SOA)**

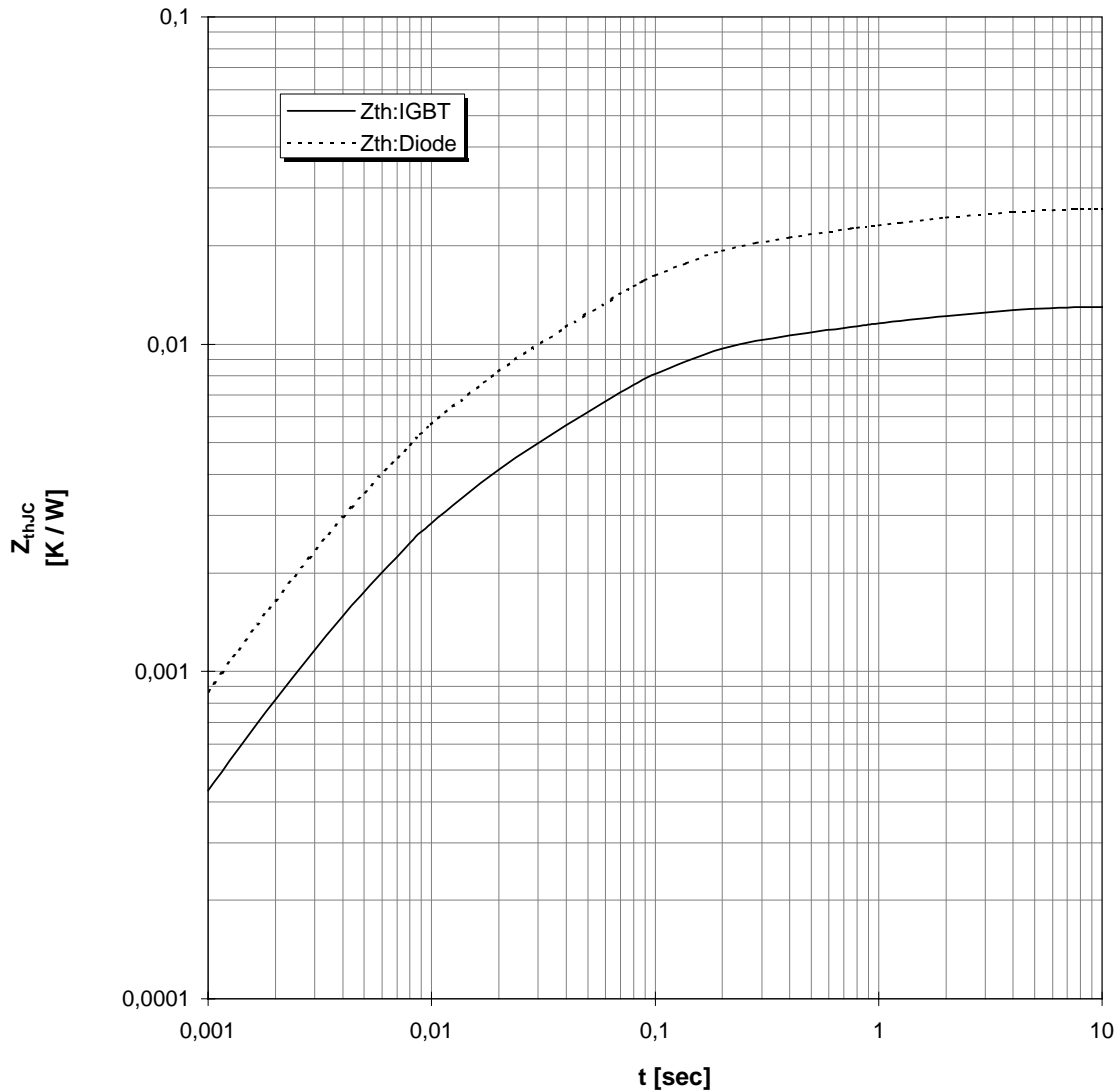
$T_{vj} = 125^\circ\text{C}$





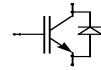
Transienter Wärmewiderstand  
Transient thermal impedance

$$Z_{thJC} = f(t)$$



i	1	2	3	4
$r_i$ [K/kW] : IGBT	2,38	6,49	1,93	2,20
$\tau_i$ [sec] : IGBT	0,0068	0,0642	0,3209	2,0212
$r_i$ [K/kW] : Diode	4,76	12,98	3,86	4,40
$\tau_i$ [sec] : Diode	0,0068	0,0642	0,3209	2,0212





Gehäusemaße / Schaltbild  
Package outline / Circuit diagram

